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 Member of Texas Instruments' Widebus™ Family 	DGG PAC (TOP V	_
 UBT[™] Transceiver Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Modes 	OEAB 1 LEAB 2 A1 3 A2 4	64 CEAB 63 CLKAB 62 B1 61 B2
 TI-OPC™ Circuitry Limits Ringing on Unevenly Loaded Backplanes 	GND 5 A3 6	60 GND 59 B3
 OEC™ Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference 	V _{CC} 7 A4 8	58 BIAS V _{CC} 57 B4
 Bidirectional Interface Between GTLP Signal Levels and LVTTL Logic Levels 	A5 9 GND 10	56 B5 55 GND
 GTLP Buffered CLKAB Signal (CLKOUT) LVTTL Interfaces Are 5-V Tolerant 	A6[] 11 A7[] 12 A8[] 13	54 B6 53 B7 52 B8
 High-Drive GTLP Outputs (100 mA) LVTTL Outputs (-24 mA/24 mA) 	GND 13 A9 14 A9 15	51 GND 50 B9
 Variable Edge-Rate Control (ERC) Input Selects GTLP Rise and Fall Times for Optimal Data-Transfer Rate and Signal Integrity in Distributed Loads 	V _{CC}	49 V _{CC} 48 B10 47 GND 46 B11
 I_{off}, Power-Up 3-State, and BIAS V_{CC} Support Live Insertion 	A12 20 GND 21	45 B12 44 GND
 Bus Hold on A-Port Data Inputs Distributed V_{CC} and GND Pins Minimize High-Speed Switching Noise 	A13 22 A14 23 GND 24 A15 25	43 B13 42 B14 41 GND 40 B15
 Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II 	V _{CC} 26 A16 27	39 V _{REF} 38 B16
 ESD Protection Exceeds JESD 22 2000-V Human-Body Model (A114-A) 200-V Machine Model (A115-A) 1000-V Charged-Device Model (C101) 	ERC 28 A17 29 CLKIN 30 OEBA 31	37 GND 36 B17 35 CLKOUT 34 CLKBA
docaviation	LEBA[[32	33 СЕВА

description

The SN74GTLPH1616 is a high-drive, 17-bit UBTTM transceiver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. It allows for transparent, latched, clocked, or clock-enabled modes of data transfer. Additionally, it provides for a copy of CLKAB at GTLP signal levels (CLKOUT) and conversion of a GTLP clock to LVTTL logic levels (CLKIN). The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard TTL or LVTTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OECTM circuitry, and TI-OPCTM circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 11 Ω.



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description (continued)

GTLP is the Texas Instruments (TITM) derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLPH1616 is given only at the preferred higher noise margin GTLP, but the user has the flexibility of using this device at either GTL ($V_{TT} = 1.2 \text{ V}$ and $V_{REF} = 0.8 \text{ V}$) or GTLP ($V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$) signal levels.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs. V_{REF} is the reference input voltage for the B port.

This device is fully specified for live-insertion applications using I_{off} , power-up 3-state, and BIAS V_{CC} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS V_{CC} circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits the overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control ($\overline{\text{ERC}}$). Changing the $\overline{\text{ERC}}$ input voltage between GND and V_{CC} adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

Active bus-hold circuitry is provided to hold unused or undriven LVTTL data inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable (\overline{OE}) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

ORDERING INFORMATION

TA	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING	
–40°C to 85°C	TSSOP – DGG	Tape and reel	SN74GTLPH1616DGGR	GTLPH1616	

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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functional description

The SN74GTLPH1616 is a high-drive (100 mA), 17-bit UBT transceiver containing D-type latches and D-type flip-flops for data-path operation in transparent, latched, clocked, or clock-enabled modes and can replace any of the functions shown in Table 1. Data polarity is noninverting.

Table 1. SN74GTLPH1616 UBT Transceiver Replacement Functions

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT	18 BIT
Transceiver	'245, '623, '645	'863	'861	'16245, '16623	'16863
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541	'16825
Latched transceiver	'543			'16543	'16472
Latch	'373, '573	'843	'841	'16373	'16843
Registered transceiver	'646, '652			'16646, '16652	'16474
Flip-flop	'374, '574		'821	'16374	
Standard UBT					'16500, '16501
Universal bus driver					'16835
Registered transceiver with clock enable	'2952			'16470, '16952	
Flip-flop with clock enable	'377	'823			'16823
Standard UBT with clock enable					'16600, '16601
SN74GTLPH	11616 UBT transcei	ver replac	es all abov	e functions	

Additionally, the device allows for transparent conversion of CLKAB-to-GTLP signal levels (CLKOUT) and CLKOUT-to-LVTTL logic levels (CLKIN).

Data flow in each direction is controlled by clock enables (\overline{CEAB} and \overline{CEBA}), latch enables (LEAB and LEBA), clock (CLKAB and CLKBA), and output enables (\overline{OEAB} and \overline{OEBA}). \overline{CEAB} and \overline{CEBA} enable all 17 bits, and \overline{OEAB} and \overline{OEBA} control the 17 bits of data and the CLKOUT/CLKIN buffered clock path for the A-to-B and B-to-A directions, respectively.

For A-to-B data flow, when $\overline{\text{CEAB}}$ is low, the device operates on the low-to-high transition of CLKAB for the flip-flop and on the high-to-low transition of LEAB for the latch path, i.e., if $\overline{\text{CEAB}}$ and LEAB are low, the A data is latched regardless of the state of CLKAB (high or low) and if LEAB is high, the device is in transparent mode. When $\overline{\text{OEAB}}$ is low, the outputs are active. When $\overline{\text{OEAB}}$ is low, the outputs are active.

The data flow for B to A is similar to A to B, except CEBA, OEBA, LEBA, and CLKBA are used.



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Function Tables

OUTPUT ENABLE†

	INPUTS					MODE
CEAB	OEAB	LEAB	CLKAB	Α	В	MODE
Х	Н	Х	Х	Χ	Z	Isolation
L	L	L	Н	Χ	В ₀ ‡ В ₀ §	Latabad storage of A data
L	L	L	L	Χ	В ₀ §	Latched storage of A data
Х	L	Н	Х	L	L	True transparent
Х	L	Н	Χ	Н	Н	True transparent
L	L	L	↑	L	L	Clasked storage of A data
L	L	L	↑	Н	Н	Clocked storage of A data
Н	L	L	Х	Χ	В ₀ §	Clock inhibit

[†] A-to-B data flow is shown: B-to-A data flow is similar, but uses CEBA, OEBA, LEBA, and CLKBA. The condition when OEAB and OEBA are both low at the same time is not recommended.

BUFFERED CLOCK

	IN	PUTS		OPERATION OR	MODE
CE	LE	OEAB	OEBA	FUNCTION	MODE
Х	Χ	Н	Н	Z	Isolation
Х	Χ	L	Н	CLKAB to CLKOUT	True delayed clock signal
Х	Χ	Н	L	CLKOUT to CLKIN	True delayed clock signal
Х	Х	L	L	CLKAB to CLKOUT, CLKOUT to CLKIN	True delayed clock signal with feedback path¶

This condition is not recommended.

B-PORT EDGE-RATE CONTROL (ERC)

INP	JT ERC	OUTPUT
LOGIC LEVEL	NOMINAL VOLTAGE	B-PORT EDGE RATE
L	GND	Slow
Н	Vcc	Fast



[‡] Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

[§] Output level before the indicated steady-state input conditions were established

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logic diagram (positive logic) V_{REF} 39 ERC 28 OEAB 1 CEAB 64 CLKAB 63 LEAB 2 LEBA 32 CLKBA 34 CEBA 33 OEBA 31 E 62 B1 1D C1 > CLK CE 1D C1 CLK < 1 of 17 Channels 35 CLKOUT CLKIN 30



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC} and BIAS V _{CC}	–0.5 V to 4.6 V
Input voltage range, V _I (see Note 1): A-port, ERC, and control inputs	–0.5 V to 7 V
B port and V _{REF}	–0.5 V to 4.6 V
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1): A port	–0.5 V to 7 V
B port	–0.5 V to 4.6 V
Current into any output in the low state, I _O : A port	48 mA
B port	200 mA
Current into any A port output in the high state, I _O (see Note 2)	48 mA
Continuous current through each V _{CC} or GND	±100 mA
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Package thermal impedance, θ _{JA} (see Note 3)	55°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.



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recommended operating conditions (see Notes 4 through 7)

			MIN	NOM	MAX	UNIT
V _{CC} , BIAS V _{CC}	Supply voltage		3.15	3.3	3.45	V
\/	Termination valtage	GTL	1.14	1.2	1.26	V
VTT	Termination voltage	GTLP	1.35	1.5	1.65	V
V	Reference voltage	GTL	0.74	0.8	0.87	V
VREF	Reference voltage	GTLP	0.87	1	1.1	V
V.	lanut voltage	B port			V_{TT}	V
VI	Input voltage	Except B port		Vcc	5.5	ľ
VIH	High-level input voltage	B port	V _{REF} +0.05			
		ERC	V _{CC} -0.6	Vcc	5.5	V
		Except B port and ERC	2			
	Low-level input voltage	B port			V _{REF} -0.05	
V_{IL}		ERC		GND	0.6	V
		Except B port and ERC			0.8	
lıK	Input clamp current	-			-18	mA
loн	High-level output current	A port			-24	mA
	Law lavel autant arreset	A port			24	A
lOL	Low-level output current	B port			100	mA
Δt/Δν	Input transition rise or fall rate	Outputs enabled			10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate	•	20			μs/V
TA	Operating free-air temperature		-40		85	°C

- NOTES: 4. All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.
 - 5. Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS V_{CC} = 3.3 V first, I/O second, and V_{CC} = 3.3 V last, because the BIAS V_{CC} precharge circuitry is disabled when any V_{CC} pin is connected. The control and V_{REF} inputs can be connected anytime, but normally are connected during the I/O stage. If B-port precharge is not required, any connection sequence is acceptable, but generally, GND is connected first.
 - 6. V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances if the dc recommended I_{OL} ratings are not exceeded.
 - 7. VREF can be adjusted to optimize noise margins, but normally is two-thirds V_{TT}. TI-OPC circuitry is enabled in the A-to-B direction and is activated when V_{TT}>0.7 V above V_{REF}. If operated in the A-to-B direction, V_{REF} should be set to within 0.6 V of V_{TT} to minimize current drain.

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electrical characteristics over recommended operating free-air temperature range for GTLP (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
٧ıK		V _{CC} = 3.15 V,	I _I = -18 mA			-1.2	V
		V _{CC} = 3.15 V to 3.45 V,	I _{OH} = -100 μA	V _{CC} -0.2			
Vон	A port	Vac - 3 15 V	I _{OH} = -12 mA	2.4			V
		V _{CC} = 3.15 V	I _{OH} = -24 mA	2			
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	I _{OL} = 100 μA			0.2	
	A port	V _{CC} = 3.15 V	I _{OL} = 12 mA			0.4	
V/01		VCC = 3.13 V	I _{OL} = 24 mA			0.5	V
VOL			$I_{OL} = 10 \text{ mA}$			0.2	V
	B port	V _{CC} = 3.15 V	I _{OL} = 64 mA			0.4	
			I _{OL} = 100 mA			0.55	
lį	Control inputs	V _{CC} = 3.45 V,	V _I = 0 or 5.5 V			±10	μΑ
. +	A port	V 0.45.V	AO = ACC			10	
lozH‡	B port	V _{CC} = 3.45 V	V _O = 1.5 V			10	μΑ
lozL‡	A and B ports	V _{CC} = 3.45 V,	V _O = GND			-10	μΑ
I _{BHL} §	A port	V _{CC} = 3.15 V,	V _I = 0.8 V	75	-		μΑ
IBHH¶	A port	V _{CC} = 3.15 V,	V _I = 2 V	-75			μΑ
I _{BHLO} #	A port	V _{CC} = 3.45 V,	$V_I = 0$ to V_{CC}	500			μΑ
Івнно		V _{CC} = 3.45 V,	$V_I = 0$ to V_{CC}	-500			μΑ
		V _{CC} = 3.45 V, I _O = 0,	Outputs high			45	
ICC	A or B port	V_I (A-port or control input) = V_{CC} or GND,	Outputs low			45	mA
		V_I (B port) = V_{TT} or GND	Outputs disabled			45	
ΔlCC☆		V_{CC} = 3.45 V, One A-port or control input at Other A-port or control inputs at V_{CC} or GNE				1.5	mA
Ci	Control inputs	V _I = 3.15 V or 0			4	5.5	pF
C.	A port	V _O = 3.15 V or 0			6.5	8	~F
C _{io}	B port or CLKOUT	V _O = 1.5 V or 0			9.5	11.5	pF
Со	CLKIN	V _O = 3.15 V or 0			4.5	5.5	pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

hot-insertion specifications for A port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS			MAX	UNIT
l _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_{I} or $V_{O} = 0$ to 5.5 V		10	μΑ
IOZPU	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 \text{ V to 3 V},$	OE = 0		±30	μΑ
IOZPD	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 V \text{ to } 3 V,$	OE = 0		±30	μΑ



For I/O ports, the parameters IOZH and IOZL include the input leakage current.

[§] The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL}max. IBHL should be measured after lowering V_{IN} to GND and then raising it to V_{II} max.

The bus-hold circuit can source at least the minimum high sustaining current at VIHmin. IBHH should be measured after raising VIN to VCC and then lowering it to VIHmin.

[#] An external driver must source at least IBHLO to switch this node from low to high.

An external driver must sink at least IBHHO to switch this node from high to low.

^{*}This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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live-insertion specifications for B port over recommended operating free-air temperature range

PARAMETER	TEST CONDITIONS			MIN	MAX	UNIT
l _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_I or $V_O = 0$ to 1.5 V		10	μΑ
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	BIAS $V_{CC} = 0$,	$V_0 = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
IOZPD	$V_{CC} = 1.5 \text{ V to } 0,$	BIAS $V_{CC} = 0$,	$V_0 = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
Inc (PIAS Van)	V _{CC} = 0 to 3.15 V	DIAC Vac - 2 15 V to 2 45 V	\/a (P.nort) - 0 to 1.5 \/		5	mA
ICC (BIAS VCC)	V _{CC} = 3.15 V to 3.45 V	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	V_O (B port) = 0 to 1.5 V		10	μΑ
VO	$V_{CC} = 0$,	BIAS $V_{CC} = 3.3 \text{ V}$	IO = 0	0.95	1.05	V
lo	$V_{CC} = 0$,	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V}$,	V_O (B port) = 0.6 V	-1	·	μΑ

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (normal mode) (unless otherwise noted)

			MIN	MAX	UNIT	
fclock	Clock frequency			175	MHz	
	t Pulse duration	LEAB or LEBA high	3		ns	
ιw.		CLKAB or CLKBA high or low	3		115	
		A before CLKAB↑	2.2			
		B before CLKBA↑	2.4			
١.	Setup time	A before LEAB↓, CLK = Don't care	1.8		ns	
t _{su}		B before LEBA↓, CLK = Don't care	2.1			
		CEAB before CLKAB↑	1.5			
		CEBA before CLKBA↑	1.5			
		A after CLKAB↑	0.7			
		B after CLKBA↑	0.5			
 	Hald time	A after LEAB↓, CLK = Don't care	1.2			
t _h	Hold time	B after LEBA↓, CLK = Don't care	0.9		ns	
		CEAB after CLKAB↑	1.5			
		CEBA after CLKBA↑	1.5			

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switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (normal mode) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	MIN	түр‡	MAX	UNIT
f _{max}				175			MHz
^t PLH	Α	В	Slow	4.3	5.6	7.1	ns
t _{PHL}	A			3.2	4.6	6.4	
^t PLH	A	В	Fast	3.2	4.3	5.6	ns
t _{PHL}				2.7	3.9	5.3	
^t PLH	LEAB	В	Slow	4.8	6.2	7.8	ns
t _{PHL}	LLAD			3.5	4.9	6.7	
^t PLH	LEAB	В	Fast	3.5	4.8	6.2	ns
t _{PHL}	LLAD			3.1	4.3	5.8	
^t PLH	CLKAB	В	Slow	4.8	6.1	7.6	ns
t _{PHL}	CLKAB	Ь	Slow	3.5	4.8	6.6	
^t PLH	CLKAB	В	Fast	3.6	4.9	6.2	ns
t _{PHL}				3.1	4.3	5.7	
^t PLH	OLKAD	CLKOUT	Slow	5.5	6.9	8.5	ns
t _{PHL}	CLKAB	CLROUT	Slow	5.5	7	9.3	
^t PLH	CLKAB	CLKOUT	Fast	4	5.3	6.7	ns
t _{PHL}				4.4	5.8	7.6	
t _{en}	OFAR	B or CLKOUT	Slow	4.8	6.2	7.8	ns
^t dis	OEAB			3.4	5.2	7.8	
t _{en}	OFAD	OEAB B or CLKOUT	Fast	3.6	4.8	6.2	ns
^t dis	UEAB			3	4.4	6.1	
	Rise time, B outputs (20% to 80%)		Slow		2.5		ns
t _r	Kise time, B outp	Fast		1.4			
+,	Fall time, B outpu	Slow		3.3		ns	
tf	raii tiirie, b outpt	Fast		2.4			
^t PLH	В	Α	_	1.1	2.8	4.3	ns
t _{PHL}	Ь			1.9	3.1	4.1	
^t PLH	LEBA	А	_	1.3	3.1	4.6	ns
t _{PHL}	LEDA			1.4	2.6	3.8	
^t PLH	CLKBA	А	_	1.3	3.3	4.8	ns
^t PHL	CLNDA			1.8	2.9	4.1	
^t PLH	CLKOUT	CLKIN		2.2	3.7	5.3	ns
^t PHL	CLKOUT	CLKIN		2.7	3.9	5.1	
^t en	- OEBA	A or CLKIN	_	1.2	2.9	4.8	ns
^t dis	UEDA			2.3	4	5.5	

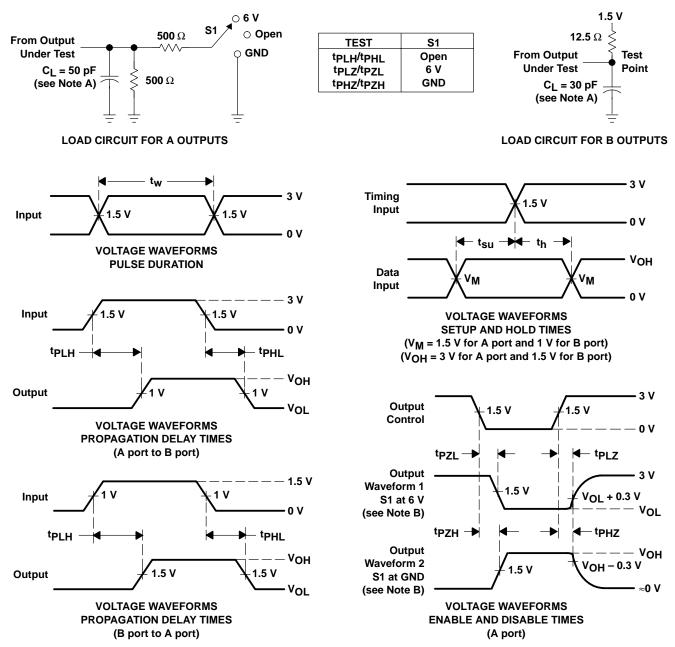
[†] Slow ($\overline{ERC} = GND$) and Fast ($\overline{ERC} = V_{CC}$)



[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

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PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \approx 10 MHz, $Z_O = 50 \Omega$, $t_f \approx 2$ ns, $t_f \approx 2$ ns.
 - D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



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DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (see Figure 1). However, the designer's backplane application probably is a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

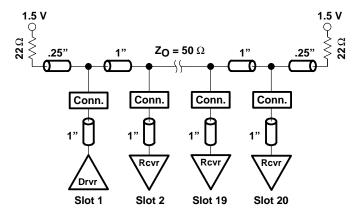


Figure 2. High-Drive Test Backplane

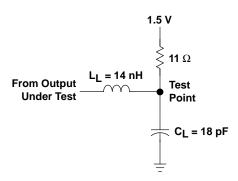


Figure 3. High-Drive RLC Network

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switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 3)

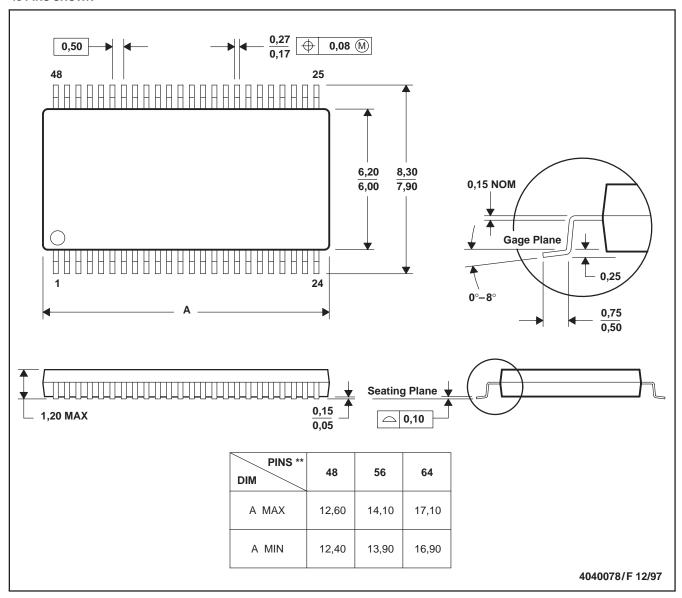
PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	түр‡	UNIT	
^t PLH	А	В	Slow	5.3	ns	
^t PHL	A			5.3		
^t PLH	Α	В	Fast	4	ns	
^t PHL	A			4		
^t PLH	LEAB	В	Slow	5.2	ns	
^t PHL	LLAD			5.2		
^t PLH	LEAB	В	Fast	3.9	ns	
^t PHL	LLAD			3.9		
^t PLH	CLK	В	Slow	5.5	ns	
^t PHL	OLK			5.5		
^t PLH	CLK	В	Fast	4.3	ns	
^t PHL	OLIK			4.3	113	
^t PLH	CLKAB	CLKOUT	Slow	5.9	ns	
^t PHL	OLIVAD			5.9		
^t PLH	CLKAB	CLKOUT	Fast	4.8	ns	
^t PHL	OLIVAD			4.8		
t _{en}	OEAB	B or CLKOUT	Slow	5.7	ns	
^t dis	OEAB			4.3		
^t en	 OEAB	B or CLKOUT	Fast	4.3	ns	
^t dis	OLAB			3.8		
	Rise time, B outp	Slow	2	ns		
t _r	Nise time, b outp	Fast	1.2	119		
+•	Fall time, B outputs (80% to 20%)		Slow	2.5	ne	
tf	raii time, b outpt	Fast	1.8	ns		

[†] Slow (\overline{ERC} = GND) and Fast (\overline{ERC} = V_{CC}) ‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C. All values are derived from TI-SPICE models.

DGG (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

48 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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